

PATENT ABSTRACTS OF JAPAN

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(71)Applicant : DAINIPPON SCREEN MFG CO LTD

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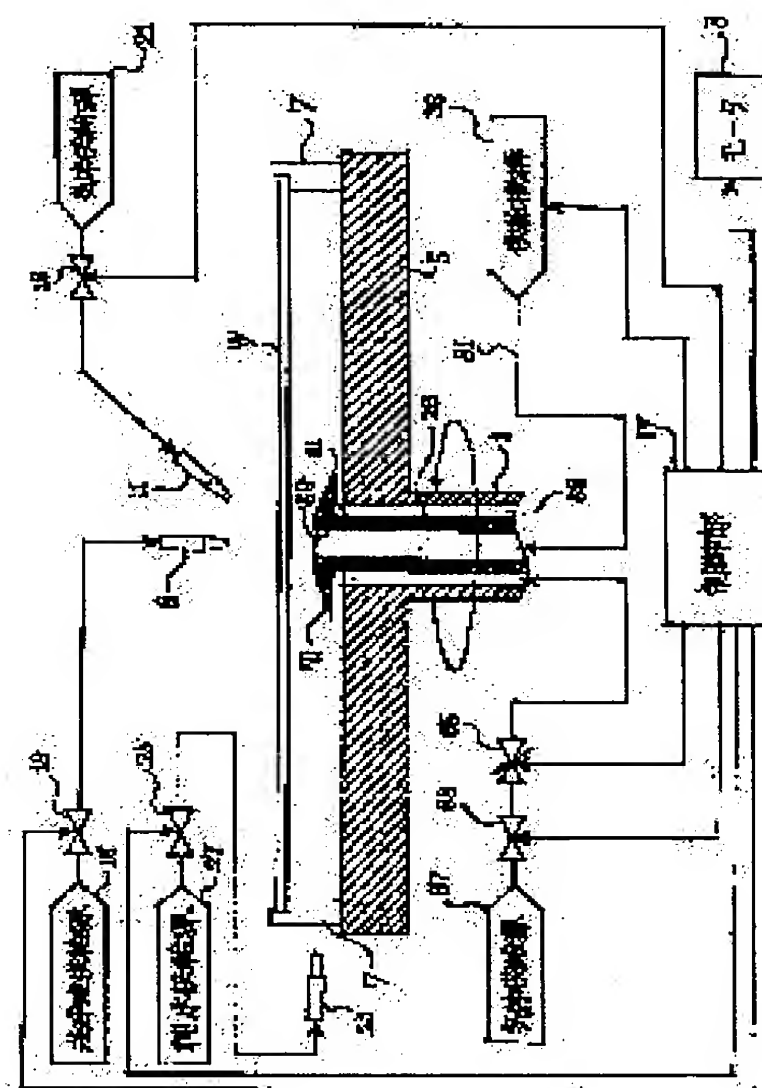
(72)Inventor : IZUMI AKIRA
MIYA KATSUHIKO
ANDO YUKITSUGU

(54) SUBSTRATE TREATMENT APPARATUS

(57)Abstract:

PROBLEM TO BE SOLVED: To prevent the contamination of the back of a substrate without performing the drying treatment of the substrate in a contaminated atmosphere of a chemical soln. contained in a washing soln.

SOLUTION: A motor 3 for rotating the spin base 5 having the surface opposed to the under surface of a wafer W to support the wafer W when the wafer W is supported in such a state that the under surface of the wafer W is allowed to be spaced apart from the opposed surface, a lower washing nozzle 29 for supplying a washing soln. to the under surface of the wafer W supported on the spin base 5, a side part washing nozzle 23 for supplying pure water different from the washing soln. to the space between the opposed surface of the spin base 5 and the under surface of the wafer W supported on the spin base 5 from the lateral side of the spin base 5 after the supply of the washing soln. to the under surface of the wafer W by the lower washing nozzle 29 are provided to a substrate treatment apparatus. Therefore, the opposed surface of the spin base 5 can be washed and the contamination of the under surface of the substrate W can be prevented without performing drying treatment in a contaminated atmosphere of the chemical soln. contained in the washing soln.



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CLAIMS

[Claim(s)]

[Claim 1] The substrate support means which is the substrate processor which performs predetermined processing to a substrate, and supports a substrate in the condition of having the inferior surface of tongue of a substrate, and the opposed face which counters, and having made the inferior surface of tongue and said opposed face of a substrate estranging, The driving means which rotates said substrate support means which supported the substrate, and a 1st processing liquid supply means to supply the 1st processing liquid to the inferior surface of tongue of the substrate supported by said substrate support means, After supplying [of the 1st processing liquid] the inferior surface of tongue of the substrate by said 1st processing liquid supply means, between the opposed face of said substrate support means, and the inferior surface of tongue of the substrate supported by said substrate support means The substrate processor characterized by having a 2nd processing liquid supply means to supply the 2nd processing liquid which is different from the 1st processing liquid from the side of said substrate support means.

[Claim 2] The 2nd processing liquid which the 1st processing liquid which is a substrate processor according to claim 1, and is supplied by said 1st processing liquid supply means is a penetrant remover containing a drug solution, and is supplied by said 2nd processing liquid supply means is a substrate processor characterized by being pure water.

[Claim 3] The substrate support means which is the substrate processor which performs predetermined processing to a substrate, and supports a substrate in the condition of having the inferior surface of tongue of a substrate, and the opposed face which counters, and having made the inferior surface of tongue and said opposed face of a substrate estranging, While supplying the 1st processing liquid to the inferior surface of tongue of the substrate supported by the driving means which rotates said substrate support means which supported the substrate, and said substrate support means A 1st processing liquid supply means to supply the different 2nd processing liquid from the 1st processing liquid after supply of the 1st processing liquid, After supplying [of the 1st processing liquid] the inferior surface of tongue of the substrate by said 1st processing liquid supply means, between the opposed face of said substrate support means, and the inferior surface of tongue of the substrate supported by said substrate support means The substrate processor characterized by having a 2nd processing liquid supply means to supply the 3rd processing liquid which is different from the 1st processing liquid from the side of said substrate support means.

[Claim 4] The 3rd processing liquid supplied by the 2nd processing liquid which the 1st processing liquid which is a substrate processor according to claim 3, and is supplied by said 1st processing liquid supply means is a penetrant remover containing a drug solution, and is supplied by said 1st processing liquid supply means, and said 2nd processing liquid supply means is a substrate processor characterized by being pure water.

[Claim 5] Where said substrate support means which is a substrate processor according to claim 4, and supported the substrate by said driving means is rotated After processing from said 1st processing liquid supply means by supplying the penetrant remover of the specified quantity to the inferior surface of tongue of a substrate, In the condition of having made it smaller than the

time of supply of the penetrant remover according either to said 1st processing liquid supply means at least of the rotational speed of said substrate support means, and the flow rate of the penetrant remover by said 1st processing liquid supply means The substrate processor characterized by having further the control means which makes pure water supply to the inferior surface of tongue of a substrate from said 1st processing liquid supply means.

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DETAILED DESCRIPTION

[Detailed Description of the Invention]

[0001]

[Industrial Application] This invention relates to the substrate processor which supplies the processing liquid which contains a drug solution in substrates, such as substrates for photo masks, such as a semi-conductor wafer and a glass substrate for liquid crystal, such as a penetrant remover and pure water, and performs predetermined processing of washing processing etc.

[0002]

[Description of the Prior Art] There is a substrate processor equipped with the spin base which supports a wafer where the inferior surface of tongue of a wafer is estranged, and the nozzle which supplies processing liquid, such as a drug solution and pure water, by the predetermined flow rate towards the inferior surface of tongue of a wafer from the center section of this spin base as this kind of a substrate processor conventionally, contacting the periphery section of the wafer which is a kind of a substrate. By making processing liquid supply to the inferior-surface-of-tongue core of a wafer by the fixed large flow rate from a nozzle, carrying out high-speed rotation of the spin base by a motor etc. in this substrate processor, where a substrate is supported Open the processing liquid supplied to the inferior-surface-of-tongue core of a wafer to the periphery side of a substrate with a centrifugal force, the whole inferior surface of tongue of a wafer is made to cover with processing liquid, dirt, such as particle adhering to the inferior surface of tongue of a wafer, is removed, and washing processing of the inferior surface of tongue of a wafer is performed.

[0003]

[Problem(s) to be Solved by the Invention] However, in the conventional substrate processor mentioned above, in case the flow rate of the processing liquid supplied to the inferior surface of tongue of a wafer displaces greatly like [the time of starting supply of processing liquid, for example from a nozzle, and at the time of stopping supply of the processing liquid from a nozzle], the condition that the processing liquid from a nozzle is not temporarily supplied appropriately towards the inferior surface of tongue of a wafer arises. Therefore, the nozzle itself and the spin base may be polluted with the drug solution contained in processing liquid.

[0004] Thus, since desiccation processing will be performed in the contamination ambient atmosphere of a drug solution at the time of subsequent spin desiccation when the nozzle itself and the spin base continue processing in the condition of having been polluted with the drug solution, there is a problem that the inferior surface of tongue of the wafer once washed with the processing liquid containing a drug solution will be polluted.

[0005] This invention is made in view of such a situation, and aims at offering the substrate processor which can prevent that do not perform desiccation processing into the contamination ambient atmosphere of a drug solution, and the inferior surface of tongue of substrates, such as a wafer, is polluted.

[0006]

[Means for Solving the Problem] In order to attain the purpose mentioned above, a substrate processor according to claim 1 The substrate support means which is the substrate processor

which performs predetermined processing to a substrate, and supports a substrate in the condition of having the inferior surface of tongue of a substrate, and the opposed face which counters, and having made the inferior surface of tongue and said opposed face of a substrate estranging, The driving means which rotates said substrate support means which supported the substrate, and a 1st processing liquid supply means to supply the 1st processing liquid to the inferior surface of tongue of the substrate supported by said substrate support means, After supplying [of the 1st processing liquid] the inferior surface of tongue of the substrate by said 1st processing liquid supply means, between the opposed face of said substrate support means, and the inferior surface of tongue of the substrate supported by said substrate support means It is characterized by having a 2nd processing liquid supply means to supply the 2nd processing liquid which is different from the 1st processing liquid from the side of said substrate support means.

[0007] According to the substrate processor according to claim 1, the 1st processing liquid is supplied to the inferior surface of tongue of a substrate with the 1st processing liquid supply means, rotating the substrate support means to which the substrate support means supported the substrate in the condition of having made the inferior surface of tongue of a substrate, and the opposed face of a substrate support means estranging, and supported the substrate in this condition by the driving means. After supply of the 1st processing liquid, the 2nd processing liquid supply means supplies the 2nd processing liquid which is different from the 1st processing liquid from the side of a substrate support means between the opposed face of a substrate support means, and the inferior surface of tongue of the substrate supported by the substrate support means. Therefore, the 1st processing liquid which has adhered to the opposed face of a substrate support means with the 2nd processing liquid after the 1st processing liquid supply is removed.

[0008] A substrate processor according to claim 2 is a substrate processor according to claim 1, and the 1st processing liquid supplied by said 1st processing liquid supply means is a penetrant remover containing a drug solution, and it is characterized by the 2nd processing liquid supplied by said 2nd processing liquid supply means being pure water.

[0009] Since according to the substrate processor according to claim 2 pure water is supplied by the 2nd processing liquid supply means from the flank of a substrate support means after a penetrant remover is supplied to the inferior surface of tongue of a substrate by the 1st processing liquid supply means, the penetrant remover adhering to a substrate support means is removed by pure water.

[0010] The substrate support means which supports a substrate in the condition that a substrate processor according to claim 3 is a substrate processor which performs predetermined processing to a substrate, has the inferior surface of tongue of a substrate, and the opposed face which counters, and made the inferior surface of tongue and said opposed face of a substrate estrange, While supplying the 1st processing liquid to the inferior surface of tongue of the substrate supported by the driving means which rotates said substrate support means which supported the substrate, and said substrate support means A 1st processing liquid supply means to supply the different 2nd processing liquid from the 1st processing liquid after supply of the 1st processing liquid, After supplying [of the 1st processing liquid] the inferior surface of tongue of the substrate by said 1st processing liquid supply means, between the opposed face of said substrate support means, and the inferior surface of tongue of the substrate supported by said substrate support means It is characterized by having a 2nd processing liquid supply means to supply the 3rd processing liquid which is different from the 1st processing liquid from the side of said substrate support means.

[0011] According to the substrate processor according to claim 3, the 1st processing liquid is supplied to the inferior surface of tongue of a substrate with the 1st processing liquid supply means, rotating the substrate support means which supported the substrate in the condition of having made the inferior surface of tongue of a substrate, and the opposed face of a substrate support means estranging, and supported the substrate in this condition by the driving means. The 2nd processing liquid which differs from the 1st processing liquid on the inferior surface of tongue of a substrate with the 1st processing liquid supply means after supply of the 1st

processing liquid is supplied. Furthermore, the 2nd processing liquid supply means supplies the 3rd processing liquid which is different from the 1st processing liquid from the side of a substrate support means between the opposed face of a substrate support means, and the inferior surface of tongue of the substrate supported by the substrate support means. Therefore, the 1st processing liquid which has adhered to the opposed face of a substrate support means with the 3rd processing liquid supplied from the 2nd processing liquid supply means after the 1st processing liquid supply is removed.

[0012] A substrate processor according to claim 4 is a substrate processor according to claim 3, and the 1st processing liquid supplied by said 1st processing liquid supply means is a penetrant remover containing a drug solution, and it is characterized by the 3rd processing liquid supplied by the 2nd processing liquid supplied by said 1st processing liquid supply means and said 2nd processing liquid supply means being pure water.

[0013] Since according to the substrate processor according to claim 4 pure water is supplied by the 2nd processing liquid supply means from the side of a substrate support means while pure water is supplied by the 1st processing liquid supply means from the lower part of a substrate after the penetrant remover which contains a drug solution with the 1st processing liquid supply means on the inferior surface of tongue of a substrate is supplied, the drug solution adhering to the opposed face of a substrate support means is removed by pure water.

[0014] Where said substrate support means which a substrate processor according to claim 5 is a substrate processor according to claim 4, and supported the substrate by said driving means is rotated After processing from said 1st processing liquid supply means by supplying the penetrant remover of the specified quantity to the inferior surface of tongue of a substrate, In the condition of having made it smaller than the time of supply of the penetrant remover according either to said 1st processing liquid supply means at least of the rotational speed of said substrate support means, and the flow rate of the penetrant remover by said 1st processing liquid supply means It is characterized by having further the control means which makes pure water supply to the inferior surface of tongue of a substrate from said 1st processing liquid supply means.

[0015] According to the substrate processor according to claim 5, where the substrate support means which supported the substrate by the driving means first is rotated, the 1st processing liquid supply means supplies the penetrant remover of the specified quantity to the inferior surface of tongue of a substrate. Then, the 1st processing liquid supply means supplies pure water to the inferior surface of tongue of a substrate in the condition of having made it smaller than the time of supply of the penetrant remover according either to the 1st processing liquid supply means at least of the rotational speed of a substrate support means, and the flow rate of the penetrant remover by the 1st processing liquid supply means. If rotational speed of a substrate support means is made small, even if the pure water supplied from the 1st processing liquid supply means arrives at the inferior surface of tongue of a substrate, it will descend to the opposed face of a substrate support means in a core, and will flow into the perimeter of a substrate support means. Moreover, if the flow rate of a penetrant remover is made small, upwards, pure water will not be supplied from the 1st processing liquid supply means, but it will descend to the opposed face of a substrate support means, and will flow into the perimeter of a substrate support means.

[0016]

[Embodiment of the Invention] Hereafter, one example of this invention is explained with reference to a drawing. Drawing 1 is drawing of longitudinal section showing the outline configuration of the substrate washing station which is a kind of the substrate processor concerning this invention, and drawing 2 is the block diagram showing the outline configuration of a feeder style shown in drawing 1.

[0017] The revolving shaft 1 in the air is connected with the revolving shaft of a motor 3, and is pivotable to the circumference of a vertical axis by the drive of this motor 3. The disc-like spin base 5 is connected with the upper limit section of this revolving shaft 1 in one. Two or more support pins 7 which support Wafer W are formed near the periphery section of the spin base 5, contacting the periphery edge of the wafer W which is a kind of a substrate. By two or more

support pins 7, Wafer W is in the condition isolated from the inferior surface of tongue of Wafer W, and the opposed face of the spin base 5 which counters between predetermined, and is supported horizontally.

[0018] In order to wash the top face of Wafer W above the spin base 5, it has the up washing nozzle 9 which supplies penetrant removers, such as pure water and a drug solution, towards near the center of rotation of the top face of Wafer W, and the up gas nozzle 11 which supplies gases, such as inert gas, such as nitrogen gas, and a dried air, to Wafer W. Besides, free passage connection of the section washing nozzle 9 is made through the closing motion valve 13 at the penetrant remover source of supply 15, and a penetrant remover is supplied to the top face of Wafer W by closing motion control of the closing motion valve 13 by the control section 17 from the up washing nozzle 9. Moreover, after continuation connection is made and the up gas nozzle 11 performs washing processing by the up washing nozzle 9 to the gas source of supply 21 through the closing motion valve 19, by closing motion control of the closing motion valve 19 by the control section 17, it supplies a gas to the top face of Wafer W from the up gas nozzle 11, and performs desiccation processing of Wafer W.

[0019] The side of the spin base 5 is equipped with the flank washing nozzle 23 which supplies pure water between the top face of the spin base 5, and the inferior surface of tongue of Wafer W. Free passage connection is made through the closing motion valve 25 at the pure-water source of supply 27, pure water passes through the space between the opposed face of the spin base 5, and the inferior surface of tongue of Wafer W from the flank washing nozzle 23, and this flank washing nozzle 23 is supplied to the opposed face of the spin base 5 by closing motion control of the closing motion valve 25 by the control section 17.

[0020] The lower penetrant remover nozzle 29 is formed in the centrum of the rotation section 1 at the same axle. Free passage connection of the feeder style 33 later mentioned through piping 31 is made at this lower penetrant remover nozzle 29.

[0021] The cylinder-like gas supply way 59 is formed in the space between the inner skin of a revolving shaft 1, and the lower washing nozzle 29, the point of this gas supply way 59 functions as a gas exhaust nozzle 61, and gases, such as nitrogen gas, are supplied to the space between the inferior surface of tongue of Wafer W, and the opposed face of the spin base 5 from the gas exhaust nozzle 61. Free passage connection of the gas exhaust nozzle 61 is made at the gas source of supply 67 through the closing motion valve 63 and flow control valve 65 in which closing motion control is carried out by the control section 17.

[0022] The umbrella type cutoff member 71 is attached in the upper limit section of the lower washing nozzle 29. This cutoff member 71 is formed in a configuration which covers the upper part of the gas exhaust nozzle 61, and the top face inclines so that it may descend towards the periphery section from the jet section 69. Although the illustration abbreviation is carried out, the gas which blew off from the gas exhaust nozzle 61 is directly supplied towards the inferior surface of tongue of Wafer W also from the stoma of a large number currently formed in the cutoff member 71, while it is supplied to the space between the inferior surface of tongue of Wafer W, and the opposed face of the spin base 5 from the clearance between the inferior surface of tongue of the cutoff member 71, and the opposed face of the spin base 5.

[0023] Next, the feeder style 33 is explained with reference to drawing 2. Drawing 2 is the block diagram showing the outline configuration of a feeder style. Free passage connection of the 1st pure-water source of supply 35 for supplying pure water to the end side of piping 31 is made, and, on the other hand, free passage connection of the lower washing nozzle 29 (refer to drawing 1) is made at the other end side. In order to adjust the flow rate of the pure water from the 1st pure-water source of supply 35, the pressure regulator 37 is formed in this piping 31. Moreover, the flowmeter 39 which measures the flow rate of the pure water from the 1st pure-water source of supply 35 is formed in the piping 31 of the downstream of this pressure regulator 37. A control section 17 asks for the difference of the flow rate measured with this flowmeter 39, and the flow rate (the 1st flow rate FV1) set up beforehand, and an electro pneumatic converter 41 adjusts the pneumatic pressure to a pressure controller 37 based on the command electrical potential difference based on this difference.

[0024] The chemical-feeding section 43 is formed in the piping 31 of the lower stream of a river

of a flowmeter 39. This chemical-feeding section 43 is equipped with three flow control valves 45, 47, and 49 equipped with the function of a closing motion valve and a flow control valve, and the closing motion valve 51 prepared in the piping 31 of the downstream of a flowmeter 39 in order to enable it to adjust respectively the injection rate of each fluid to piping 31 independently.

[0025] The 1st drug solution source of supply 53 is open for free passage, and the 1st flow control valve 45 adjusts the injection rate of the 1st drug solution to piping 31, and the 2nd flow control valve 47 is opened for free passage by the 2nd drug solution source of supply 55, and it adjusts the injection rate of the 2nd drug solution to piping 31. Moreover, the 2nd pure-water source of supply 57 is open for free passage, and the 3rd flow control valve 57 adjusts the injection rate of the pure water to piping 31.

[0026] In addition, all of closing motion control of the closing motion valve 51 and flow control valves 45, 47, and 49 are controlled by the control section 17 in generalization. Moreover, flow control valves 45, 47, and 49 are beforehand set up so that it may become a predetermined flow rate, and especially the flow rate adjusted by the 3rd flow control valve 49 is adjusted so that it may become the 2nd flow rate FV2 smaller than the 1st flow rate FV1 beforehand set up by the pressure controller 37.

[0027] In case washing processing of the inferior surface of tongue of Wafer W is carried out, a control section 17 opens the closing motion valve 51 wide. While it is adjusted so that it may become the 1st flow rate FV1 with a pressure controller 37 through an electro pneumatic converter 41, and supplying the pure water from the 1st pure-water source of supply 35 to piping 31 It is adjusted so that it may become the 2nd flow rate FV2 smaller than the 1st flow rate FV1 by the 3rd flow control valve 49, and the pure water from the 2nd pure-water source of supply 57 is poured in to piping 31. Moreover, flow control valves 45 and 47 are adjusted and the 1st or/and the 2nd drug solution of requirements are poured in to piping 31. Therefore, the penetrant remover with which the necessary drug solution was mixed only for requirements by the pure water of a large flow rate with which the 1st flow rate FV1 and 2nd flow rate FV2 were doubled is supplied to the inferior surface of tongue of Wafer W.

[0028] Moreover, in case the jet section 69 and the covered member 71 of the lower washing nozzle 29 to which the penetrant remover adhered are washed, the closing motion valve 51 and flow control valves 45 and 47 are stopped, and it is adjusted so that it may become the 2nd flow rate FV2 of a small flow rate from the 1st flow rate FV1 by the flow control valve 49, and only pure water is poured in from the 2nd pure-water source of supply 57 to piping 31. At this time, by opening the closing motion valve 25 shown in drawing 1, pure water passes through the space between the opposed face of the spin base 5, and the inferior surface of tongue of Wafer W from the flank washing nozzle 23, and a control section 17 is supplied to the opposed face of the spin base 5.

[0029] Next, actuation of a substrate processor is explained, referring to the flow chart of drawing 3. In addition, it omits about the explanation of operation with the up washing nozzle 9 and the up gas nozzle 11 which are prepared above Wafer W.

[0030] First, a control section 17 carries out the roll control of the motor 3, and carries out high-speed rotation of the wafer W at the 1st rotational frequency (step S1). The rotational frequency at this time is for example, 600rpm extent. With rotation initiation at the 1st rotational frequency of Wafer W, a control section 17 While supplying the pure water adjusted so that the closing motion valve 51 might be opened wide and it might become the 1st flow rate FV1 (a part for for example, 2.4l./) with a pressure controller 37 through an electro pneumatic converter 41 to piping 31 from the 1st pure-water source of supply 35 The pure water adjusted so that it might become the 2nd flow rate FV2 (a part for for example, 0.5l./) by the flow control valve 49 is poured in from the 2nd pure-water source of supply 57 to piping 31. Furthermore, the drug solution of the specified quantity is poured in to piping 31 through flow control valves 45 and 47 from the 1st drug solution source of supply 53 and the 2nd drug solution source of supply 55. The penetrant remover with which the drug solution was mixed by the pure water of a large flow rate (a part for 2.9l./[This example]) with which the 1st flow rate FV1 and 2nd flow rate FV2 were doubled is supplied to the inferior surface of tongue of Wafer W from the exhaust nozzle 69

of the lower washing nozzle 29, and the inferior surface of tongue of Wafer W is washed by the penetrant remover. (Step S2)

[0031] Therefore, with rotation of the wafer W in the 1st rotational frequency, a penetrant remover moves toward the periphery section from the inferior surface of tongue of the core of Wafer W, and it disperses around while a penetrant remover makes the penetrant remover supplied by the large flow rate supply with sufficient vigor to the inferior surface of tongue of Wafer W from the jet section 69. In addition, the drop containing the particle adhering to the droplet of the penetrant remover which contains a drug solution at this time, and the inferior surface of tongue of Wafer W adheres to the cutoff member 71 of the lower washing nozzle 29, or the opposed face of the spin base 5.

[0032] Next, a control section 17 stops the condition and flow control valves 45 and 47 holding the 1st rotational frequency in step S1 mentioned above, and suspends the impregnation to the piping 31 of a drug solution. Therefore, since only pure water is supplied to the inferior surface of tongue of Wafer W from the lower washing nozzle 29 by the large flow rate (a part for 2.9l./) at Wafer W, washing by the pure water to the inferior surface of tongue of Wafer W which was touching the penetrant remover is performed (step S3). In addition, at this time, it continues being in the condition in which the drop of a penetrant remover adhered to the cutoff member 71 of the lower washing nozzle 29, or the opposed face of the spin base 5.

[0033] A control section 17 carries out the roll control of the motor 3, and rotates Wafer W rather than the 1st rotational frequency at the 2nd rotational frequency which is a low speed (step S4). The rotational frequency at this time is for example, 20rpm extent. A control section 17 opens the closing motion valve 25 wide, and starts supply of pure water from the pure-water source of supply 27 through the flank washing nozzle 23 with rotation initiation of the 2nd rotational frequency of Wafer W to the space between the inferior surface of tongue of Wafer W, and the opposed face of the spin base 5. Moreover, while stopping a shut-off valve 51, a flow control valve 49 is considered as [the condition of having opened wide]. Consequently, the pure water adjusted so that it might become a small flow rate (a part for 0.5l./) by the flow control valve 49 is poured in from the 2nd pure-water source of supply 57 to piping 31, and it is supplied from the lower washing nozzle 29. Therefore, it flows down to the covered member 71 of the lower washing nozzle 29, without going upwards, pure water moves toward the periphery section with rotation of the wafer W in the 2nd rotational frequency from the inferior surface of tongue of Wafer W, and the pure water supplied by the small flow rate disperses around. At this time, the drop of the penetrant remover adhering to the exhaust nozzle 69 and the covered member 71 of the lower washing nozzle 29 is removed (step S5).

[0034] A control section 17 carries out the roll control of the motor 3, and rotates Wafer W rather than the 2nd rotational frequency at the 3rd rotational frequency which is a low speed further (step S6). The rotational frequency at this time is for example, 10rpm extent. a control section 17 carries out the closedown of the flow control valve 49 -- while taking, the closing motion valve 51 is opened wide and control of a pressure controller 37 is resumed. Thereby, from the lower washing nozzle 29, the pure water of the 1st flow rate FV1 (a part for 2.4l./) is supplied. Therefore, although the pure water supplied from the exhaust nozzle 69 of the lower washing nozzle 29 goes to the inferior surface of tongue of Wafer W, with rotation of the wafer W in the 3rd rotational frequency, somewhat, pure water falls from the center of rotation of Wafer W, to the opposed face of the spin base 5 toward the periphery section, when it spreads to some extent, breadth and, and flows down toward the periphery section. Thereby, the drop of the penetrant remover adhering to the opposed face of the spin base 5 is removed (step S7).

[0035] Next, a control section 17 rotates Wafer W at the 1st rotational frequency (600rpm) again (step S8). And a control section 17 opens a flow control valve 49 wide, and pure water is supplied to the inferior surface of tongue of the wafer W by which high-speed rotation is carried out by the large flow rate (a part for 2.9l./) from the lower washing nozzle 29. Therefore, the inferior surface of tongue of Wafer W is again washed by pure water like SUTTEPU S3 mentioned above (step S9).

[0036] Next, a control section 17 stops the closing motion valve 51, and suspends supply of the pure water from the lower washing nozzle 29 while it stops a flow control valve 49. Moreover, a

control section 17 carries out the blade latch also of the closing motion valve 25, and also suspends supply of pure water between the inferior surface of tongue of the wafer W from the flank washing nozzle 23, and the opposed face of the spin base 5. On the other hand, while opening the closing motion valve 63 shown in drawing 1, it passes along the gas supply way 59 from the gas source of supply 67, and the inert gas adjusted to the proper flow rate by the flow control valve 65 is supplied towards the inferior surface of tongue of Wafer W from the gas exhaust nozzle 61. And rotation of a motor 3 is further set as the 4th high-speed rotational frequency (for example, 3000rpm) from the 1st rotational frequency (step S10). Thereby, while Wafer W rotates at high speed, inert gas is supplied to the inferior surface of tongue of Wafer W, and desiccation processing of Wafer W is performed (step S11).

[0037] After desiccation processing of this step S11 is completed, a control section 17 also suspends rotation of Wafer W with a drive halt of a motor 3 (step S12). In this, actuation of single string washing processing and desiccation processing stops.

[0038] As mentioned above, in case the inferior surface of tongue of Wafer W is washed In case a penetrant remover is supplied by the maximum flow rate and the lower washing nozzle 29 is washed While carrying out low-speed rotation of the wafer W, in case pure water is supplied by the minimum flow rate and the opposed face of the spin base 5 is washed Since pure water was supplied by the middle flow rate while carrying out low-speed rotation of the wafer W The lower washing nozzle 29 and the opposed face of the spin base 5 can be washed only by comparatively easy control of actuation / un-operating. [of a motor 3, flow control valves 45, 47, and 49 and a pressure controller 37, and the closing motion valve 51] Therefore, pure water can wash the lower washing nozzle 29 which became dirty from the penetrant remover at the time of washing of the wafer W by the penetrant remover containing a drug solution etc., and the opposed face of the spin base 5.

[0039] Moreover, since pure water is supplied from the flank washing nozzle 23 between the inferior surface of tongue of Wafer W, and the opposed face of the spin base 5 in case the lower washing nozzle 29 and the opposed face of the spin base 5 are washed, at the time of subsequent desiccation processing, it can prevent un-arranging [with which Wafer W is polluted by the adhering penetrant remover].

[0040]

[Effect of the Invention] As explained in full detail above, according to the substrate processor according to claim 1, the 2nd processing liquid supply means after supply of the 1st processing liquid between the opposed face of a substrate support means, and the inferior surface of tongue of the substrate supported by the substrate support means Since the 2nd processing liquid which is different from the 1st processing liquid from the side of a substrate support means is supplied Contamination of the inferior surface of tongue of a substrate can be prevented without being able to remove the 1st processing liquid which has adhered to the opposed face of a substrate support means with the 2nd processing liquid, and performing desiccation processing in the contamination ambient atmosphere of the 1st processing liquid after the 1st processing liquid supply.

[0041] Since pure water is supplied by the 2nd processing liquid supply means from the flank of a substrate support means after the penetrant remover which contains a drug solution with the 1st processing liquid supply means on the inferior surface of tongue of a substrate is supplied according to the substrate processor according to claim 2, the penetrant remover containing the drug solution adhering to a substrate support means can remove with pure water, and contamination of the inferior surface of tongue of a substrate can prevent, without performing desiccation processing in the contamination ambient atmosphere of the drug solution contained in a penetrant remover.

[0042] According to the substrate processor according to claim 3, the 2nd processing liquid which differs from the 1st processing liquid on the inferior surface of tongue of a substrate with the 1st processing liquid supply means after supply of the 1st processing liquid is supplied. Furthermore, since the 2nd processing liquid supply means supplies the 3rd processing liquid which is different from the 1st processing liquid from the side of a substrate support means between the opposed face of a substrate support means, and the inferior surface of tongue of

the substrate supported by the substrate support means Contamination of the inferior surface of tongue of a substrate can be prevented without being able to remove the 1st processing liquid which has adhered to the opposed face of a substrate support means with the 3rd processing liquid supplied from the 2nd processing liquid supply means, and performing desiccation processing in the contamination ambient atmosphere of the 1st processing liquid after the 1st processing liquid supply.

[0043] After the penetrant remover which contains a drug solution with the 1st processing liquid supply means on the inferior surface of tongue of a substrate is supplied, while pure water is supplied by the 1st processing liquid supply means from the lower part of a substrate according to the substrate processor according to claim 4 Since pure water is supplied by the 2nd processing liquid supply means from the side of a substrate support means, the penetrant remover containing the drug solution adhering to the opposed face of a substrate support means can remove with pure water, and contamination of the inferior surface of tongue of a substrate can be prevented, without performing desiccation processing in the contamination ambient atmosphere of the drug solution contained in a penetrant remover.

[0044] Where the substrate support means which supported the substrate by the driving means is rotated according to the substrate processor according to claim 5 After the 1st processing liquid supply means supplies the penetrant remover of the specified quantity to the inferior surface of tongue of a substrate, in the condition of having made it smaller than the time of supply of the penetrant remover according either to the 1st processing liquid supply means at least of the rotational speed of a substrate support means, and the flow rate of the penetrant remover by the 1st processing liquid supply means Since the 1st processing liquid supply means supplies pure water to the inferior surface of tongue of a substrate, it can descend to the opposed face of a substrate support means, can flow into the perimeter of a substrate support means, and pure water can wash efficiently the substrate maintenance means and the 1st processing liquid supply means which became dirty from the penetrant remover containing a drug solution. Consequently, contamination of the inferior surface of tongue of a substrate can be prevented still more effectively, without performing desiccation processing in the contamination ambient atmosphere of the drug solution contained in a penetrant remover.

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(71) 出願人 000207551
大日本スクリーン製造株式会社
京都府京都市上京区堀川通寺之内上る4丁目天神北町1番地の1

(72) 発明者 泉 昭
京都市上京区堀川通寺之内上る4丁目天神北町1番地の1 大日本スクリーン製造株式会社内

(72) 発明者 宮 勝彦
京都市上京区堀川通寺之内上る4丁目天神北町1番地の1 大日本スクリーン製造株式会社内

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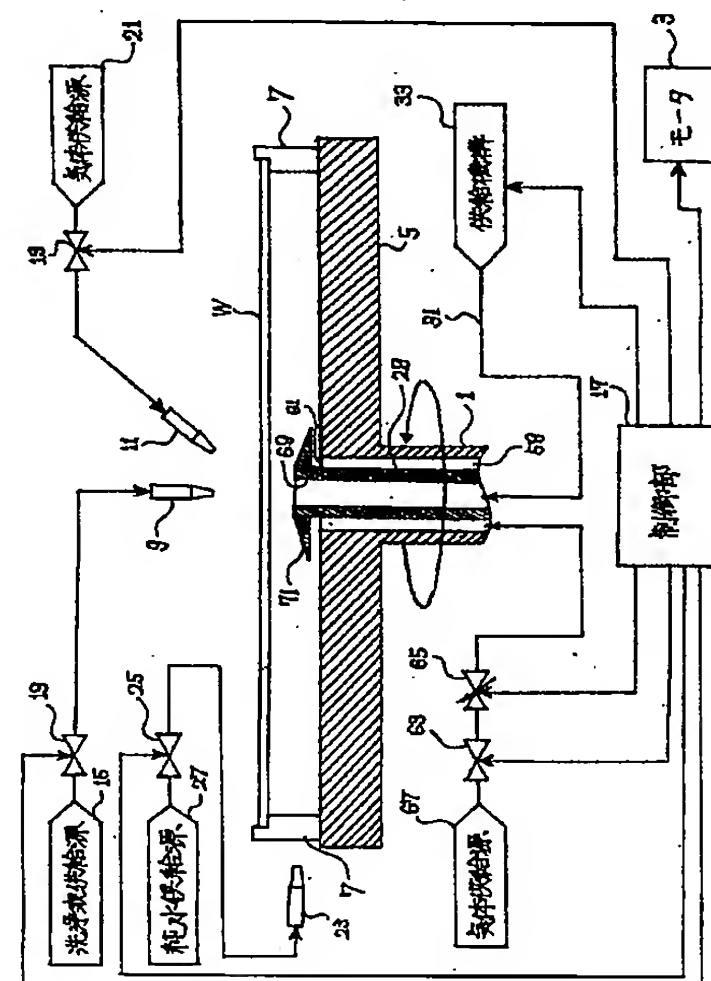
(54) 【発明の名称】 基板処理装置

(57) 【要約】

【課題】 洗浄液に含まれる薬液の汚染雰囲気中で乾燥処理を行うことがなく、基板の下面が汚染されることを防止できる。

【解決手段】 ウエハWの下面と対向する対向面を有し、かつウエハWの下面と対向面とを離間させた状態でウエハWを支持すると、ウエハWを支持したスピンドル5を回転させるモータ3と、スピンドル5に支持されたウエハWの下面に洗浄液を供給する下部洗浄ノズル29と、下部洗浄ノズル29によるウエハWの下面への洗浄液の供給後に、スピンドル5の対向面とスピンドル5に支持されたウエハWの下面との間に、スピンドル5の側方から洗浄液とは異なる純水を供給する側部洗浄ノズル23と、を備える。したがって、スピンドル5の対向面を洗浄でき、洗浄液に含まれる薬液の汚染雰囲気中で乾燥処理を行うことなく、基板Wの下面が汚染されることを防止できる。

【発明名】 図面
【図1】



【特許請求の範囲】

【請求項1】 基板に所定の処理を行う基板処理装置であって、
基板の下面と対向する対向面を有し、かつ基板の下面と前記対向面とを離間させた状態で基板を支持する基板支持手段と、
基板を支持した前記基板支持手段を回転させる駆動手段と、
前記基板支持手段に支持された基板の下面に第1処理液を供給する第1 処理液供給手段と、
前記第1 処理液供給手段による基板の下面への第1 処理液の供給後に、前記基板支持手段の対向面と前記基板支持手段に支持された基板の下面との間に、前記基板支持手段の側方から第1 処理液とは異なる第2 処理液を供給する第2処理液供給手段と、
を備えたことを特徴とする基板処理装置。

【請求項2】 請求項1に記載の基板処理装置であって、前記第1 処理液供給手段により供給される第1 処理液は薬液を含む洗浄液であり、前記第2 処理液供給手段により供給される第2 処理液は純水であることを特徴とする基板処理装置。

【請求項3】 基板に所定の処理を行う基板処理装置であって、
基板の下面と対向する対向面を有し、かつ基板の下面と前記対向面とを離間させた状態で基板を支持する基板支持手段と、
基板を支持した前記基板支持手段を回転させる駆動手段と、
前記基板支持手段に支持された基板の下面に第1処理液を供給するとともに、第1 処理液の供給後に第1 処理液とは異なる第2 処理液を供給する第1 処理液供給手段と、
前記第1 処理液供給手段による基板の下面への第1 処理液の供給後に、前記基板支持手段の対向面と前記基板支持手段に支持された基板の下面との間に、前記基板支持手段の側方から第1 処理液とは異なる第3 処理液を供給する第2処理液供給手段と、
を備えたことを特徴とする基板処理装置。

【請求項4】 請求項3に記載の基板処理装置であって、前記第1 処理液供給手段により供給される第1 処理液は薬液を含む洗浄液であり、前記第1 処理液供給手段により供給される第2 処理液および前記第2 処理液供給手段により供給される第3 処理液は純水であることを特徴とする基板処理装置。

【請求項5】 請求項4に記載の基板処理装置であって、前記駆動手段により基板を支持した前記基板支持手段を回転させた状態で、前記第1 処理液供給手段から所定量の洗浄液を基板の下面に供給して処理を行った後、前記基板支持手段の回転速度および前記第1 処理液供給手段による洗浄液の流量の少なくともいずれか一方を前記第

1 処理液供給手段による洗浄液の供給時よりも小さくした状態で、前記第1 処理液供給手段から基板の下面に純水を供給させる制御手段をさらに備えたことを特徴とする基板処理装置。

【発明の詳細な説明】

【0001】

【産業上の利用分野】 本発明は、半導体ウエハ、液晶用ガラス基板等、フォトリソ用基板等の基板に薬液を含む洗浄液、純水等の処理液を供給して洗浄処理等の所定の処理を行う基板処理装置に関する。

【0002】

【従来の技術】 従来この種の基板処理装置として、基板の一種であるウエハの周縁部に当接しつつウエハの下面を離間した状態でウエハを支持するスピンドルと、このスピンドルの中央部からウエハの下面へ向けて、薬液、純水等の処理液を所定の流量で供給するノズルとを備えた基板処理装置がある。この基板処理装置においては、基板を支持した状態でスピンドルをモータ等で高速回転させつつ、ノズルから一定の大流量で処理液をウエハの下面中心部に供給させることにより、ウエハの下面中心部に供給された処理液を遠心力で基板の外周側へ広げて、ウエハの下面全体を処理液で覆わせ、ウエハの下面に付着したパーティクル等の汚れを除去してウエハの下面の洗浄処理を行っている。

【0003】

【発明が解決しようとする課題】 しかしながら、上述した従来の基板処理装置では、例えばノズルから処理液の供給を開始した時点や、ノズルからの処理液の供給を停止させた時点のように、ウエハの下面に供給される処理液の流量が大きく変位する際には、一時的にノズルからの処理液がウエハの下面へ向けて適切に供給されない状態が生じる。そのため、ノズル自身やスピンドルが処理液に含まれる薬液等によって汚染されることがある。

【0004】 このようにノズル自身やスピンドルが薬液で汚染された状態で処理を継続してしまうと、その後のスピンドル乾燥時には薬液の汚染雰囲気中で乾燥処理を行うことになるため、薬液を含む処理液によって一旦洗浄されたウエハの下面が汚染されてしまうという問題がある。

【0005】 本発明は、このような事情に鑑みてなされたものであって、薬液の汚染雰囲気中に乾燥処理を行うことがなく、ウエハ等の基板の下面が汚染されることを防止できる基板処理装置を提供することを目的とする。

【0006】

【課題を解決するための手段】 上述した目的を達成するために、請求項1に記載の基板処理装置は、基板に所定の処理を行う基板処理装置であって、基板の下面と対向する対向面を有し、かつ基板の下面と前記対向面とを離間させた状態で基板を支持する基板支持手段と、基板を支持した前記基板支持手段を回転させる駆動手段と、前

記基板支持手段に支持された基板の下面に第1処理液を供給する第1処理液供給手段と、前記第1処理液供給手段による基板の下面への第1処理液の供給後に、前記基板支持手段の対向面と前記基板支持手段に支持された基板の下面との間に、前記基板支持手段の側方から第1処理液とは異なる第2処理液を供給する第2処理液供給手段と、を備えたことを特徴とするものである。

【0007】請求項1に記載の基板処理装置によれば、基板支持手段が基板の下面と基板支持手段の対向面とを離間させた状態で基板を支持し、この状態で基板を支持した基板支持手段を駆動手段により回転させながら、第1処理液供給手段により基板の下面に第1処理液を供給する。第1処理液の供給後に、第2処理液供給手段が、基板支持手段の対向面と基板支持手段に支持された基板の下面との間に、基板支持手段の側方から第1処理液とは異なる第2処理液を供給する。したがって、第1処理液供給後に、第2処理液により基板支持手段の対向面に付着している第1処理液が除去される。

【0008】請求項2に記載の基板処理装置は、請求項1に記載の基板処理装置であって、前記第1処理液供給手段により供給される第1処理液は薬液を含む洗浄液であり、前記第2処理液供給手段により供給される第2処理液は純水であることを特徴とするものである。

【0009】請求項2に記載の基板処理装置によれば、第1処理液供給手段により基板の下面に洗浄液が供給された後、基板支持手段の側部から第2処理液供給手段により純水が供給されるので、基板支持手段に付着している洗浄液が純水により除去される。

【0010】請求項3に記載の基板処理装置は、基板に所定の処理を行う基板処理装置であって、基板の下面と対向する対向面を有し、かつ基板の下面と前記対向面とを離間させた状態で基板を支持する基板支持手段と、基板を支持した前記基板支持手段を回転させる駆動手段と、前記基板支持手段に支持された基板の下面に第1処理液を供給するとともに、第1処理液の供給後に第1処理液とは異なる第2処理液を供給する第1処理液供給手段と、前記第1処理液供給手段による基板の下面への第1処理液の供給後に、前記基板支持手段の対向面と前記基板支持手段に支持された基板の下面との間に、前記基板支持手段の側方から第1処理液とは異なる第3処理液を供給する第2処理液供給手段と、を備えたことを特徴とするものである。

【0011】請求項3に記載の基板処理装置によれば、基板の下面と基板支持手段の対向面とを離間させた状態で基板を支持し、この状態で基板を支持した基板支持手段を駆動手段により回転させながら、第1処理液供給手段により基板の下面に第1処理液を供給する。第1処理液の供給後に、第1処理液供給手段により基板の下面に第1処理液とは異なる第2処理液を供給する。さらに、第2処理液供給手段が、基板支持手段の対向面と基板支持手

段に支持された基板の下面との間に、基板支持手段の側方から第1処理液とは異なる第3処理液を供給する。したがって、第1処理液供給後に、第2処理液供給手段から供給される第3処理液により基板支持手段の対向面に付着している第1処理液が除去される。

【0012】請求項4に記載の基板処理装置は、請求項3に記載の基板処理装置であって、前記第1処理液供給手段により供給される第1処理液は薬液を含む洗浄液であり、前記第1処理液供給手段により供給される第2処理液および前記第2処理液供給手段により供給される第3処理液は純水であることを特徴とするものである。

【0013】請求項4に記載の基板処理装置によれば、第1処理液供給手段により基板の下面に薬液を含む洗浄液が供給された後、基板の下方から第1処理液供給手段により純水が供給されるとともに、基板支持手段の側方から第2処理液供給手段により純水が供給されるので、基板支持手段の対向面に付着している薬液が純水により除去される。

【0014】請求項5に記載の基板処理装置は、請求項4に記載の基板処理装置であって、前記駆動手段により基板を支持した前記基板支持手段を回転させた状態で、前記第1処理液供給手段から所定量の洗浄液を基板の下面に供給して処理を行った後、前記基板支持手段の回転速度および前記第1処理液供給手段による洗浄液の流量の少なくともいずれか一方を前記第1処理液供給手段による洗浄液の供給時よりも小さくした状態で、前記第1処理液供給手段から基板の下面に純水を供給させる制御手段をさらに備えたことを特徴とするものである。

【0015】請求項5に記載の基板処理装置によれば、まず駆動手段により基板を支持した基板支持手段を回転させた状態で、第1処理液供給手段が所定量の洗浄液を基板の下面に供給する。その後、基板支持手段の回転速度および第1処理液供給手段による洗浄液の流量の少なくともいずれか一方を第1処理液供給手段による洗浄液の供給時よりも小さくした状態で、第1処理液供給手段が基板の下面に純水を供給する。基板支持手段の回転速度を小さくすると、第1処理液供給手段から供給される純水が基板の下面に達しても中心部で基板支持手段の対向面に降下して、基板支持手段の周囲に流れ出る。また、洗浄液の流量を小さくすると、第1処理液供給手段から純水は上方へは供給されず、基板支持手段の対向面に降下して、基板支持手段の周囲に流れ出る。

【0016】

【発明の実施の形態】以下、図面を参照して本発明の一実施例を説明する。図1は、本発明に係る基板処理装置の一種である基板洗浄装置の概略構成を示す縦断面図であり、図2は、図1中に示す供給機構の概略構成を示すブロック図である。

【0017】中空の回転軸1は、モータ3の回転軸に連結されており、このモータ3の駆動により鉛直軸周りに

回転可能である。この回転軸 1 の上端部には、円板状のスピンベース 5 が一体的に連結されている。スピンベース 5 の周縁部付近には、基板の一種であるウエハ W の外周端部に当接しつつウエハ W を支持する支持ピン 7 が複数本設けられている。ウエハ W は、複数本の支持ピン 7 によって、ウエハ W の下面と対向するスピンベース 5 の対向面から所定の間隔離した状態で、水平に支持されている。

【0018】スピンベース 5 の上方には、ウエハ W の上面を洗浄するためにウエハ W の上面の回転中心付近に向けて純水、薬液等の洗浄液を供給する上部洗浄ノズル 9 と、窒素ガス等の不活性ガスやドライエア等の気体をウエハ W に供給する上部ガスノズル 11 とが備えられている。この上部洗浄ノズル 9 は、開閉弁 13 を介して洗浄液供給源 15 に連通接続されており、制御部 17 による開閉弁 13 の開閉制御によって上部洗浄ノズル 9 からウエハ W の上面に洗浄液が供給される。また、上部ガスノズル 11 は、開閉弁 19 を介して気体供給源 21 に連通接続されており、上部洗浄ノズル 9 による洗浄処理を行った後、制御部 17 による開閉弁 19 の開閉制御によって上部ガスノズル 11 からウエハ W の上面に気体を供給して、ウエハ W の乾燥処理を行う。

【0019】スピンベース 5 の側方には、スピンベース 5 の上面とウエハ W の下面との間に純水を供給する側部洗浄ノズル 23 が備えられている。この側部洗浄ノズル 23 は、開閉弁 25 を介して純水供給源 27 に連通接続されており、制御部 17 による開閉弁 25 の開閉制御によって側部洗浄ノズル 23 から純水がスピンベース 5 の対向面とウエハ W の下面との間の空間を通過してスピンベース 5 の対向面へ供給される。

【0020】回転部 1 の中空部には、下部洗浄液ノズル 29 が同軸に設けられている。この下部洗浄液ノズル 29 には、配管 31 を介して後述する供給機構 33 が連通接続されている。

【0021】回転軸 1 の内周面と下部洗浄ノズル 29 との間の空間には、円筒状の気体供給路 59 が形成されており、この気体供給路 59 の先端部は気体噴出口 61 として機能し、気体噴出口 61 からウエハ W の下面とスピンベース 5 の対向面との間の空間に窒素ガス等の気体が供給される。気体噴出口 61 は、制御部 17 により開閉制御される開閉弁 63 と流量調節弁 65 とを介して気体供給源 67 に連通接続されている。

【0022】下部洗浄ノズル 29 の上端部には、傘型の遮断部材 71 が取り付けられている。この遮断部材 71 は、気体噴出口 61 の上方を覆うような形状に形成されており、上面は噴出口 61 から周縁部に向けて下降するように傾斜している。気体噴出口 61 から噴出された気体は、遮断部材 71 の下面とスピンベース 5 の対向面との隙間から、ウエハ W の下面とスピンベース 5 の対向面との間の空間に供給されるとともに、図示省略されてい

るが遮断部材 71 に形成されている多数の小孔からもウエハ W の下面へ向けて直接供給される。

【0023】次に、供給機構 33 について図 2 を参照して説明する。図 2 は、供給機構の概略構成を示すブロック図である。配管 31 の一端側には純水を供給するための第 1 の純水供給源 35 が連通接続されており、一方、他端側には下部洗浄ノズル 29 (図 1 参照) が連通接続されている。この配管 31 には、第 1 の純水供給源 35 からの純水の流量を調整するために圧力調整器 37 が設けられている。また、この圧力調整器 37 の下流側の配管 31 には、第 1 の純水供給源 35 からの純水の流量を計測する流量計 39 が設けられている。この流量計 39 で計測された流量と予め設定されている流量 (第 1 の流量 F V 1) との差分を制御部 17 が求め、この差分に基づく指令電圧に基づいて電空変換器 41 が圧力調節器 37 への空気圧を調整する。

【0024】流量計 39 の下流の配管 31 には薬液注入部 43 が設けられている。この薬液注入部 43 は、配管 31 への各流体の注入量を各々独立に調整することができるようにするために、開閉弁と流量調節弁との機能を備えた 3 つの流量調節弁 45, 47, 49 と、流量計 39 の下流側の配管 31 に設けられた開閉弁 51 とを備えている。

【0025】第 1 の流量調節弁 45 は、第 1 の薬液供給源 53 に連通されており、配管 31 に対する第 1 の薬液の注入量を調整し、第 2 の流量調節弁 47 は、第 2 の薬液供給源 55 に連通されており、配管 31 に対する第 2 の薬液の注入量を調整する。また、第 3 の流量調節弁 57 は、第 2 の純水供給源 57 に連通されており、配管 31 に対する純水の注入量を調整する。

【0026】なお、開閉弁 51 と流量調節弁 45, 47, 49 の開閉制御は、すべて制御部 17 によって統括的に制御される。また、流量調節弁 45, 47, 49 は、所定の流量となるように予め設定されており、特に、第 3 の流量調節弁 49 により調整される流量は、圧力調節器 37 によって予め設定されている第 1 の流量 F V 1 よりも少ない第 2 の流量 F V 2 になるように調整されている。

【0027】ウエハ W の下面を洗浄処理する際には、制御部 17 は開閉弁 51 を開放し、電空変換器 41 を介して圧力調節器 37 により第 1 の流量 F V 1 になるように調整されて第 1 の純水供給源 35 からの純水を配管 31 へ供給するとともに、第 3 の流量調節弁 49 により第 1 の流量 F V 1 よりも少ない第 2 の流量 F V 2 になるように調整されて第 2 の純水供給源 57 からの純水を配管 31 へ注入する。また、流量調節弁 45, 47 を調整して所要量の第 1 または / および第 2 の薬液を配管 31 へ注入する。したがって、第 1 の流量 F V 1 と第 2 の流量 F V 2 とを合わせた大流量の純水に所要の薬液が所要量だけ混合された洗浄液がウエハ W の下面へ供給される。

【0028】また、洗浄液が付着した下部洗浄ノズル29の噴出口69や遮蔽部材71を洗浄する際には、開閉弁51、流量調節弁45、47を閉止し、流量調節弁49により第1の流量FV1よりも小流量の第2の流量FV2になるように調整されて、第2の純水供給源57から純水のみを配管31へ注入する。このとき、制御部17は、図1に示す開閉弁25を開放することによって、純水が側部洗浄ノズル23からスピンベース5の対向面とウエハWの下面との間の空間を通過してスピンベース5の対向面へ供給される。

【0029】次に、基板処理装置の動作について、図3のフローチャートを参照しながら説明する。なお、ウエハWの上方に設けられている上部洗浄ノズル9と上部ガスノズル11との動作説明については省略する。

【0030】まず、制御部17は、モータ3を回転制御してウエハWを第1の回転数で高速回転させる（ステップS1）。このときの回転数は、例えば、600rpm程度である。ウエハWの第1の回転数での回転開始とともに、制御部17は、開閉弁51を開放し、電空変換器41を介して圧力調節器37により第1の流量FV1（例えば、2.4リットル/分）となるように調整された純水を第1の純水供給源35から配管31へ供給するとともに、流量調節弁49により第2の流量FV2（例えば、0.5リットル/分）となるように調整された純水を第2の純水供給源57から配管31へ注入する。さらに、流量調節弁45、47を介して所定量の薬液を第1の薬液供給源53および第2の薬液供給源55から配管31へ注入し、第1の流量FV1と第2の流量FV2とを合わせた大流量（この例では、2.9リットル/分）の純水に薬液が混合された洗浄液が下部洗浄ノズル29の噴出口69からウエハWの下面へ供給され、ウエハWの下面が洗浄液により洗浄される。（ステップS2）

【0031】したがって、大流量で供給された洗浄液は、洗浄液が勢いよく噴出口69からウエハWの下面に供給させるとともに、第1の回転数でのウエハWの回転に伴い、洗浄液がウエハWの中心部の下面から周縁部に向かって移動して周囲に飛散する。なお、このとき薬液を含む洗浄液の飛沫や、ウエハWの下面に付着していたパーティクルを含む液滴が下部洗浄ノズル29の遮断部材71やスピンベース5の対向面に付着する。

【0032】次に、制御部17は、上述したステップS1での第1の回転数を保持した状態、流量調節弁45、47を閉止して、薬液の配管31への注入を停止する。したがって、ウエハWには純水だけが大量（2.9リットル/分）で下部洗浄ノズル29からウエハWの下面に供給されるので、洗浄液に触れていたウエハWの下面への純水による洗浄が行われる（ステップS3）。なお、この時点では、下部洗浄ノズル29の遮断部材71やスピンベース5の対向面には、洗浄液の液滴が付着し

た状態のままである。

【0033】制御部17は、モータ3を回転制御してウエハWを第1の回転数よりも低速である第2の回転数で回転させる（ステップS4）。このときの回転数は、例えば、20rpm程度である。ウエハWの第2の回転数の回転開始とともに、制御部17は、開閉弁25を開放し、純水供給源27から側部洗浄ノズル23を介して、ウエハWの下面とスピンベース5の対向面との間の空間に純水の供給を開始する。また、閉止弁51を閉止するとともに、流量調節弁49は開放した状態のままとする。その結果、流量調節弁49により小流量（0.5リットル/分）となるように調整された純水を第2の純水供給源57から配管31へ注入され、下部洗浄ノズル29から供給される。したがって、小流量で供給される純水は、上方へ向かうことなく下部洗浄ノズル29の遮蔽部材71に流下し、第2の回転数でのウエハWの回転に伴い純水がウエハWの下面から周縁部に向かって移動して周囲に飛散する。このとき、下部洗浄ノズル29の噴出口69と遮蔽部材71に付着している洗浄液の液滴は除去される（ステップS5）。

【0034】制御部17は、モータ3を回転制御してウエハWを第2の回転数よりもさらに低速である第3の回転数で回転させる（ステップS6）。このときの回転数は、例えば、10rpm程度である。制御部17は、流量調節弁49を閉止させるとともに、開閉弁51を開放し、圧力調節器37の制御を再開する。これにより、下部洗浄ノズル29からは第1の流量FV1（2.4リットル/分）の純水が供給される。したがって、下部洗浄ノズル29の噴出口69から供給される純水はウエハWの下面へ向かうが、第3の回転数でのウエハWの回転に伴い純水がウエハWの回転中心から周縁部へ向かって多少広がり、ある程度広がった時点でスピンベース5の対向面に落下して周縁部へ向かって流下する。これにより、スピンベース5の対向面に付着していた洗浄液の液滴が除去される（ステップS7）。

【0035】次に、制御部17は、ウエハWを再び第1の回転数（600rpm）で回転させる（ステップS8）。そして、制御部17は、流量調節弁49を開放し、高速回転されているウエハWの下面には下部洗浄ノズル29から純水が大量（2.9リットル/分）で供給される。そのため、上述したステップS3と同様に、再びウエハWの下面が純水で洗浄される（ステップS9）。

【0036】次に、制御部17は、流量調節弁49を閉止するとともに、開閉弁51を閉止して、下部洗浄ノズル29からの純水の供給を停止する。また、制御部17は、開閉弁25も閉止し、側部洗浄ノズル23からのウエハWの下面とスピンベース5の対向面との間に純水の供給も停止する。一方、図1に示す開閉弁63を開放するとともに、流量調節弁65により適宜の流量に調整し

た不活性ガスを気体供給源 67 から気体供給路 59 を通
って、気体噴出口 61 からウエハ W の下面へ向けて供給
する。そして、モータ 3 の回転を第 1 の回転数からさら
に高速の第 4 の回転数（例えば、3000 rpm）に設
定される（ステップ S10）。これにより、ウエハ W は
高速で回転されながら、不活性ガスがウエハ W の下面へ
供給され、ウエハ W の乾燥処理が行われる（ステップ S
11）。

【0037】このステップ S11 の乾燥処理が終了した
後、制御部 17 は、モータ 3 の駆動停止に伴い、ウエハ
W の回転も停止する（ステップ S12）。これにより、
一連洗浄処理及び乾燥処理の動作は停止する。

【0038】上述したように、ウエハ W の下面を洗浄す
る際には、洗浄液を最大の流量で供給し、下部洗浄ノズ
ル 29 を洗浄する際には、ウエハ W を低速回転させると
ともに最小の流量で純水を供給し、スピンベース 5 の対
向面を洗浄する際には、ウエハ W を低速回転させるとと
もに中間の流量で純水を供給するようにしたので、モー
タ 3 と流量調節弁 45、47、49、圧力調節器 37、
開閉弁 51 の作動／非作動といった比較的簡単な制御だ
けで、下部洗浄ノズル 29 やスピンベース 5 の対向面を
洗浄することができる。したがって、薬液等を含む洗浄
液によるウエハ W の洗浄時に洗浄液で汚れた下部洗浄ノ
ズル 29 やスピンベース 5 の対向面を純水で洗浄するこ
とができる。

【0039】また、下部洗浄ノズル 29 やスピンベース
5 の対向面を洗浄する際には、側部洗浄ノズル 23 から
純水をウエハ W の下面とスピンベース 5 の対向面との間
に供給しているので、その後の乾燥処理時には、付着し
ていた洗浄液によってウエハ W が汚染されるような不都
合を防止できる。

【0040】

【発明の効果】以上詳述したように、請求項 1 に記載の
基板処理装置によれば、第 1 処理液の供給後に、第 2 処
理液供給手段が、基板支持手段の対向面と基板支持手段
に支持された基板の下面との間に、基板支持手段の側方
から第 1 処理液とは異なる第 2 処理液を供給するので、
第 1 処理液供給後に、第 2 処理液により基板支持手段の
対向面に付着している第 1 処理液を除去でき、また第 1
処理液の汚染雰囲気中で乾燥処理を行うこともなく、基
板の下面の汚染を防止できる。

【0041】請求項 2 に記載の基板処理装置によれば、
第 1 処理液供給手段により基板の下面に薬液を含む洗浄
液が供給された後、基板支持手段の側部から第 2 処理液
供給手段により純水が供給されるので、基板支持手段に
付着している薬液を含む洗浄液が純水により除去でき、
洗浄液に含まれる薬液の汚染雰囲気中で乾燥処理を行う
こともなく、基板の下面の汚染を防止できる。

【0042】請求項 3 に記載の基板処理装置によれば、

第 1 処理液の供給後に、第 1 処理液供給手段により基板の
下面に第 1 処理液とは異なる第 2 処理液を供給し、さら
に、第 2 処理液供給手段が、基板支持手段の対向面と基
板支持手段に支持された基板の下面との間に、基板支持
手段の側方から第 1 処理液とは異なる第 3 処理液を供給
しているので、第 1 処理液供給後に、第 2 処理液供給手
段から供給される第 3 処理液により基板支持手段の対向
面に付着している第 1 処理液を除去でき、また第 1 処理
液の汚染雰囲気中で乾燥処理を行うこともなく、基板の
下面の汚染を防止できる。

【0043】請求項 4 に記載の基板処理装置によれば、
第 1 処理液供給手段により基板の下面に薬液を含む洗浄
液が供給された後、基板の下方から第 1 処理液供給手段
により純水が供給されるとともに、基板支持手段の側方
から第 2 処理液供給手段により純水が供給されるので、
基板支持手段の対向面に付着している薬液を含む洗浄液
が純水により除去でき、洗浄液に含まれる薬液の汚染雰
囲気中で乾燥処理を行うこともなく、基板の下面の汚染
を防止できる。

【0044】請求項 5 に記載の基板処理装置によれば、
駆動手段により基板を支持した基板支持手段を回転させ
た状態で、第 1 処理液供給手段が所定量の洗浄液を基板
の下面に供給した後、基板支持手段の回転速度および第
1 処理液供給手段による洗浄液の流量の少なくともいず
れか一方を第 1 処理液供給手段による洗浄液の供給時よ
り小さくした状態で、第 1 処理液供給手段が基板の下
面に純水を供給しているので、基板支持手段の対向面に
降下して、基板支持手段の周囲に流れ出て、薬液を含む
洗浄液で汚れた基板保持手段や第 1 処理液供給手段を純
水で効率的に洗浄することができる。その結果、洗浄液
に含まれる薬液の汚染雰囲気中で乾燥処理を行うことも
なく、基板の下面の汚染をさらに効果的に防止できる。

【図面の簡単な説明】

【図 1】本発明に係る基板処理装置の概略構成を示す縦
断面図である。

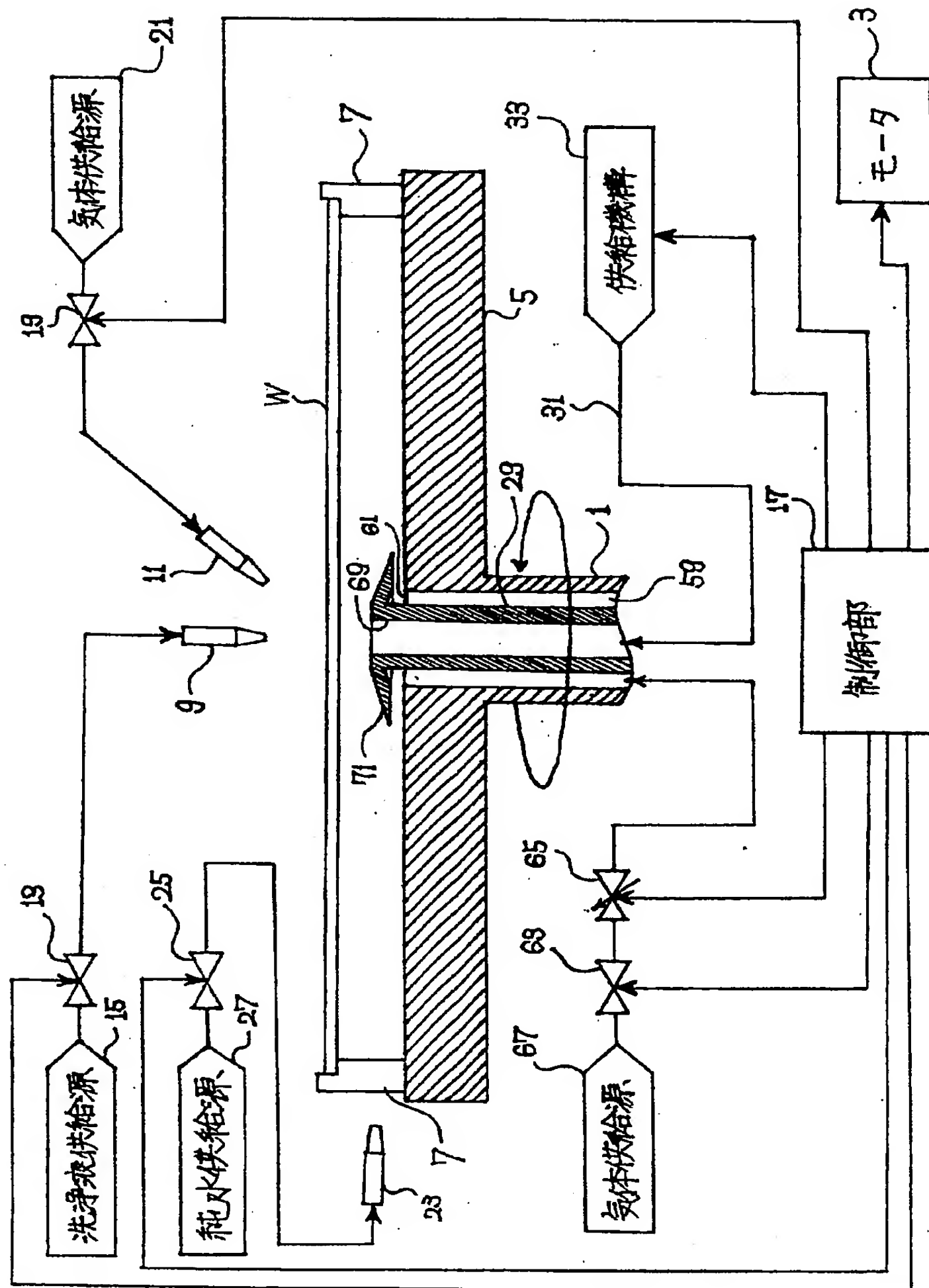
【図 2】供給機構の概略構成を示す図である。

【図 3】本発明に係る基板処理装置の動作を示すフロー
チャートである。

【符号の説明】

W … ウエハ
1 … 回転軸
3 … モータ
5 … スピンベース
7 … 支持ピン
17 … 制御部
23 … 側部洗浄ノズル
29 … 下部洗浄ノズル
33 … 供給機構

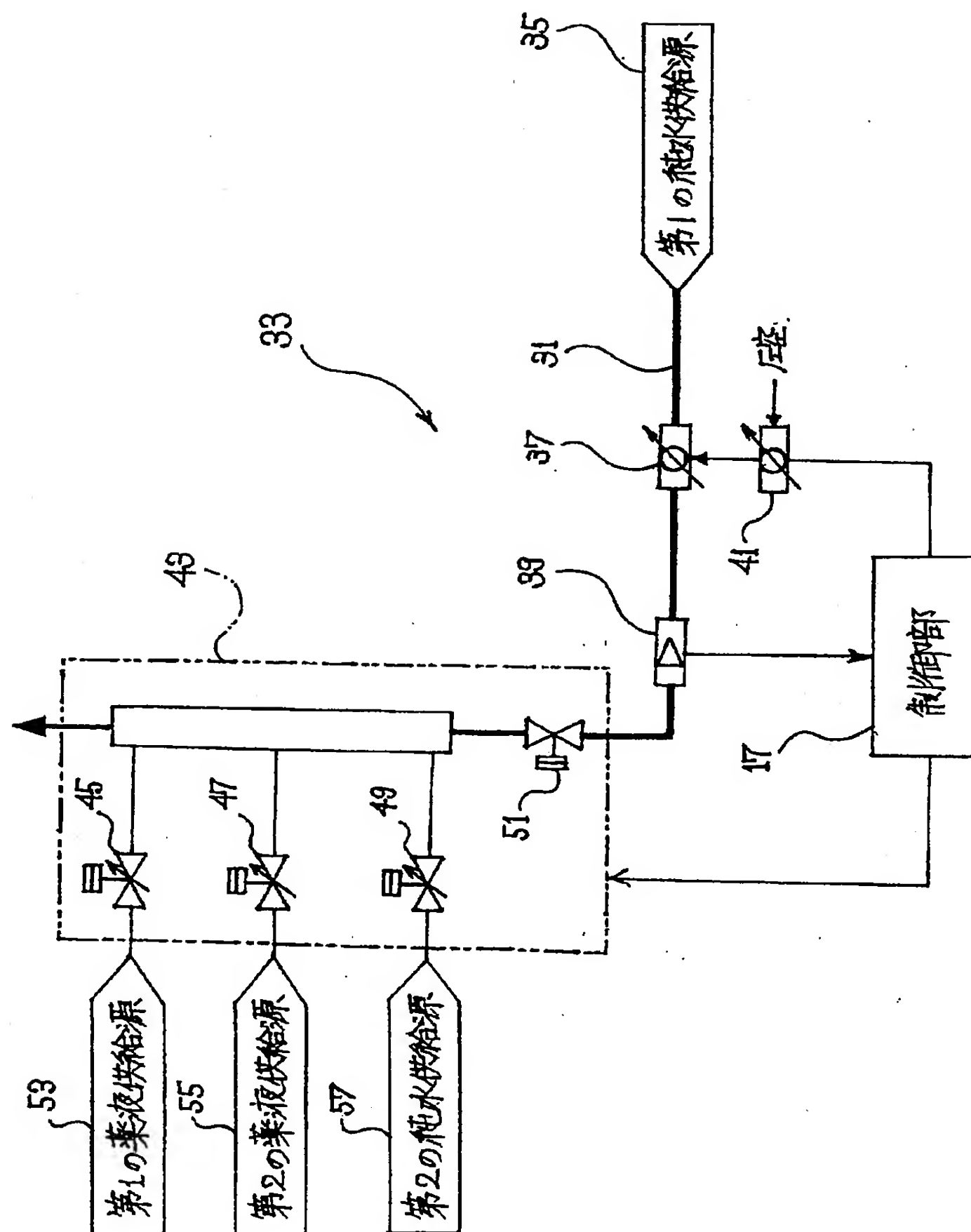
【 例 1 】



【図2】

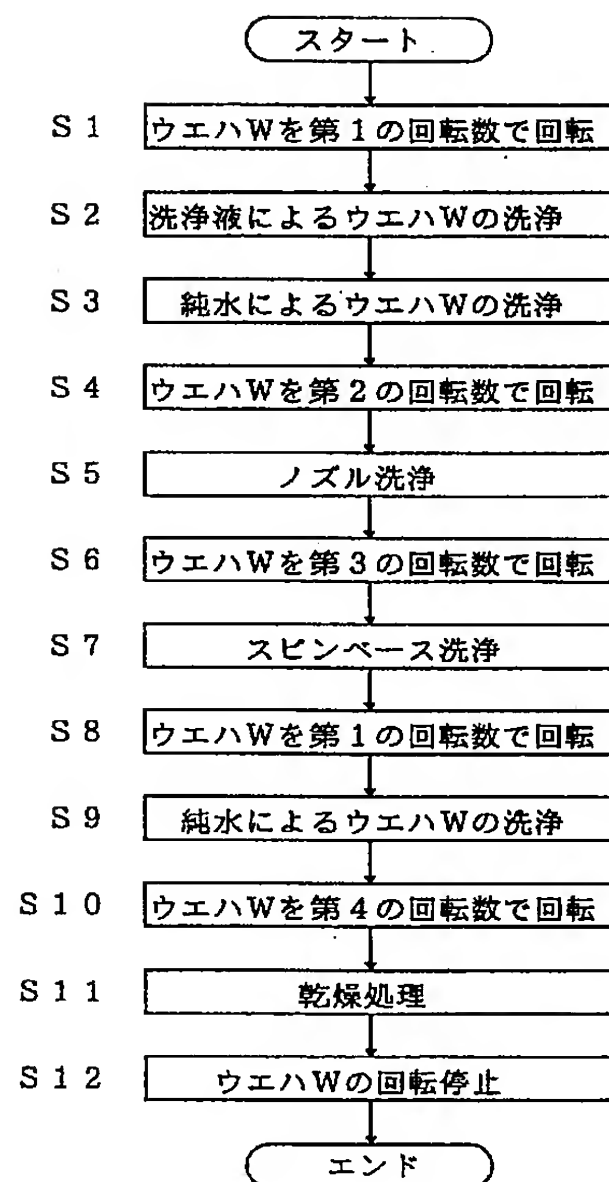
【書類名】 図面

【図2】



【図 3】

【書類名】 図面
【図 3】



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(72)発明者 安藤 幸嗣
京都市上京区堀川通寺之内上る4丁目天神
北町1番地の1 大日本スクリーン製造株
式会社内

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